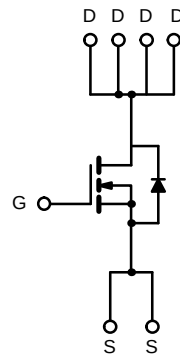
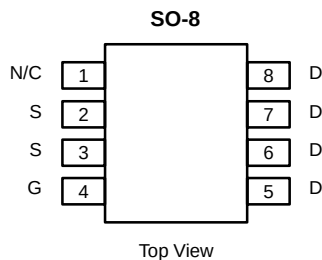


**N-Channel Enhancement-Mode MOSFET****PRODUCT SUMMARY**

| <b>V<sub>DS</sub> (V)</b> | <b>R<sub>DS(ON)</sub> (Ω)</b> | <b>I<sub>D</sub> (A)</b> |
|---------------------------|-------------------------------|--------------------------|
| 200                       | 1.0 @ V <sub>GS</sub> = 10 V  | ±1.0                     |



N-Channel MOSFET

**ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)**

| <b>PARAMETER</b>                                               |                       | <b>SYMBOL</b>                     | <b>LIMIT</b> | <b>UNIT</b> |
|----------------------------------------------------------------|-----------------------|-----------------------------------|--------------|-------------|
| Drain-Source Voltage                                           |                       | V <sub>DS</sub>                   | 200          | V           |
| Gate-Source Voltage                                            |                       | V <sub>GS</sub>                   | ±20          |             |
| Continuous Drain Current (T <sub>J</sub> = 150°C) <sup>A</sup> | T <sub>A</sub> = 25°C | I <sub>D</sub>                    | ±1.0         | A           |
|                                                                | T <sub>A</sub> = 70°C |                                   | ±0.8         |             |
| Pulsed Drain Current                                           |                       | I <sub>DM</sub>                   | ±10          |             |
| Avalanche Current                                              |                       | I <sub>AS</sub>                   | 5            | mJ          |
| Single Avalanche Energy                                        |                       | E <sub>AS</sub>                   | 1.3          |             |
| Continuous Source Current (Diode Conduction) <sup>A</sup>      |                       | I <sub>S</sub>                    | 1.0          | A           |
| Maximum Power Dissipation <sup>A</sup>                         | T <sub>A</sub> = 25°C | P <sub>D</sub>                    | 2.5          | W           |
|                                                                | T <sub>A</sub> = 70°C |                                   | 1.6          |             |
| Operating Junction and Storage Temperature Range               |                       | T <sub>J</sub> , T <sub>stg</sub> | -55 to 150   | °C          |

**THERMAL RESISTANCE RATINGS**

| <b>PARAMETER</b>                         | <b>SYMBOL</b>     | <b>LIMIT</b> | <b>UNIT</b> |
|------------------------------------------|-------------------|--------------|-------------|
| Maximum Junction-to-Ambient <sup>A</sup> | R <sub>thJA</sub> | 50           | °C/W        |

## Notes

A. Surface Mounted on FR4 Board, t ≤ 10 sec.

Updates to this data sheet may be obtained via facsimile by calling Siliconix FaxBack, 1-408-970-5600. Please request FaxBack document #70123.

**SPECIFICATIONS (T<sub>J</sub> = 25°C UNLESS OTHERWISE NOTED)**

| PARAMETER                                     | SYMBOL              | TEST CONDITION                                                                                                           | MIN | TYP <sup>A</sup> | MAX  | UNIT |
|-----------------------------------------------|---------------------|--------------------------------------------------------------------------------------------------------------------------|-----|------------------|------|------|
| <b>STATIC</b>                                 |                     |                                                                                                                          |     |                  |      |      |
| Gate Threshold Voltage                        | V <sub>GS(th)</sub> | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA                                                              | 2   |                  |      | V    |
| Gate-Body Leakage                             | I <sub>GSS</sub>    | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V                                                                           | 2   |                  | ±100 | nA   |
| Zero Gate Voltage Drain Current               | I <sub>DSS</sub>    | V <sub>DS</sub> = 160 V, V <sub>GS</sub> = 0 V                                                                           |     |                  | 2    | μA   |
|                                               |                     | V <sub>DS</sub> = 160 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55°C                                                    |     |                  | 25   |      |
| On-State Drain Current <sup>B</sup>           | I <sub>D(on)</sub>  | V <sub>DS</sub> ≥ 10 V, V <sub>GS</sub> = 10 V                                                                           | 5.0 |                  |      | A    |
| Drain-Source On-State Resistance <sup>B</sup> | r <sub>DS(on)</sub> | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 1.0 A                                                                           |     | 0.8              | 1.0  | Ω    |
| Forward Transconductance <sup>B</sup>         | g <sub>fs</sub>     | V <sub>DS</sub> = 15 V, I <sub>D</sub> = 1.0 A                                                                           |     | 1.5              |      | S    |
| Diode Forward Voltage <sup>B</sup>            | V <sub>SD</sub>     | I <sub>S</sub> = 1.0 A, V <sub>GS</sub> = 0 V                                                                            |     | 0.7              | 1.2  | V    |
| <b>DYNAMIC<sup>A</sup></b>                    |                     |                                                                                                                          |     |                  |      |      |
| Total Gate Charge                             | Q <sub>g</sub>      | V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 1.0 A                                                  |     | 8.6              | 16   | nC   |
| Gate-Source Charge                            | Q <sub>gs</sub>     |                                                                                                                          |     | 1.5              |      |      |
| Gate-Drain Charge                             | Q <sub>gd</sub>     |                                                                                                                          |     | 3.2              |      |      |
| Turn-On Delay Time                            | t <sub>d(on)</sub>  | V <sub>DD</sub> = 100 V, R <sub>L</sub> = 100 Ω<br>I <sub>D</sub> = 1.0 A, V <sub>GEN</sub> = 10 V, R <sub>G</sub> = 6 Ω |     | 7                | 14   | ns   |
| Rise Time                                     | t <sub>r</sub>      |                                                                                                                          |     | 12               | 24   |      |
| Turn-Off Delay Time                           | t <sub>d(off)</sub> |                                                                                                                          |     | 26               | 50   |      |
| Fall Time                                     | t <sub>f</sub>      |                                                                                                                          |     | 15               | 30   |      |
| Source-Drain Reverse Recovery Time            | t <sub>rr</sub>     | I <sub>F</sub> = 1.0 A, di/dt = 100 A/μs                                                                                 |     | 130              |      |      |

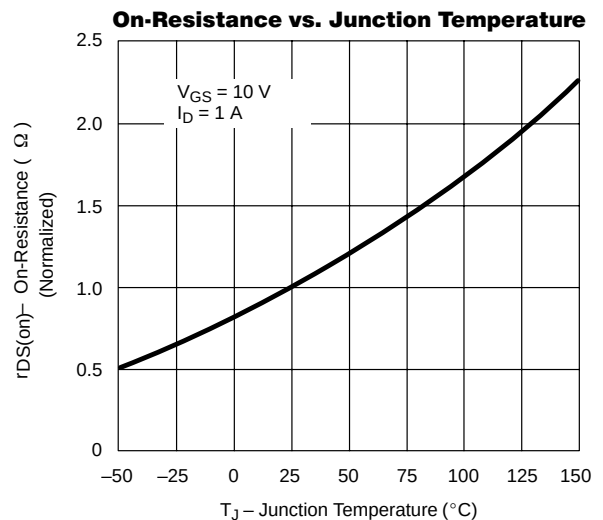
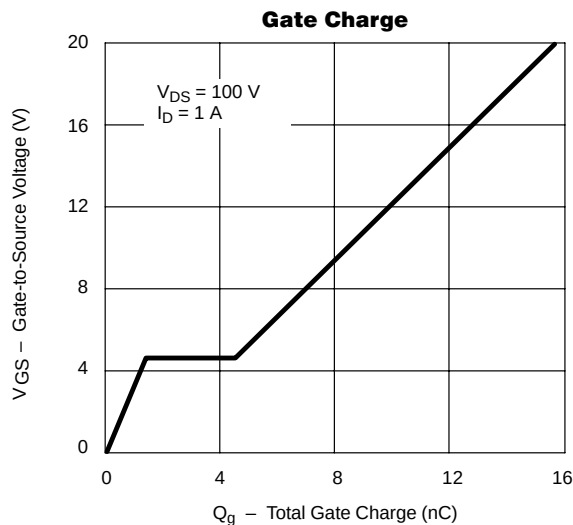
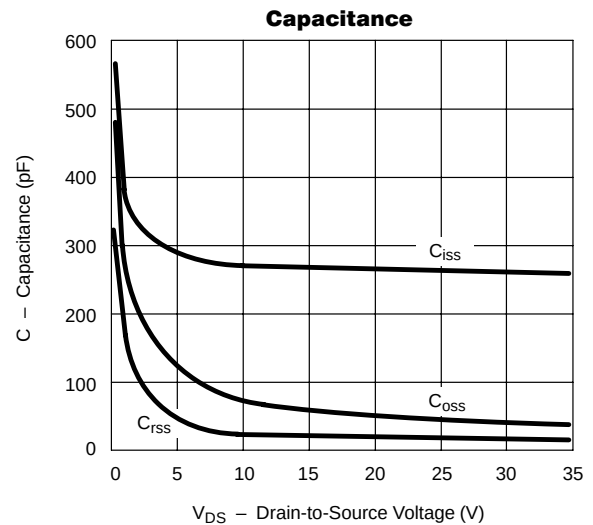
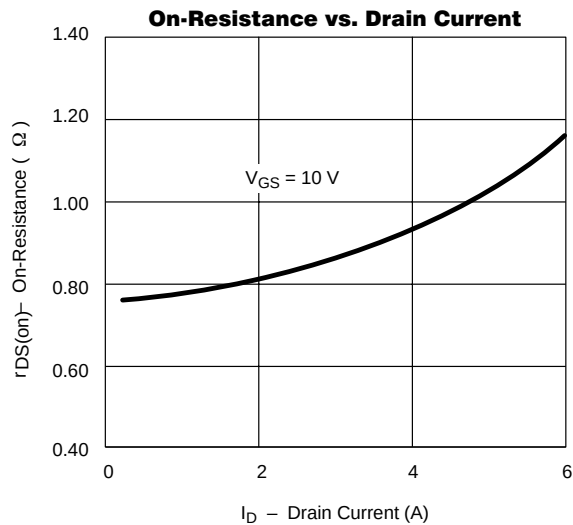
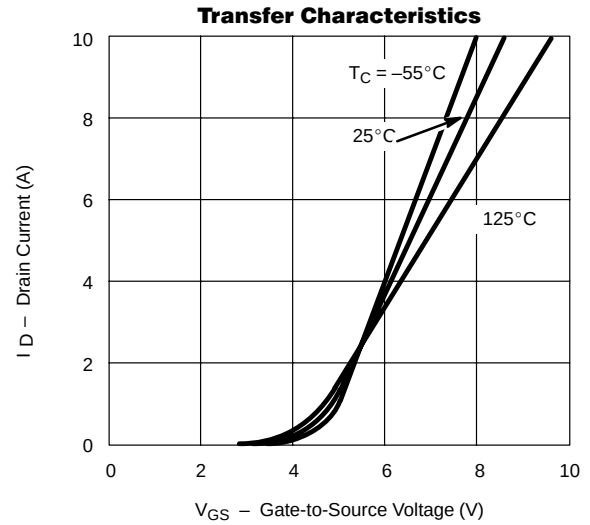
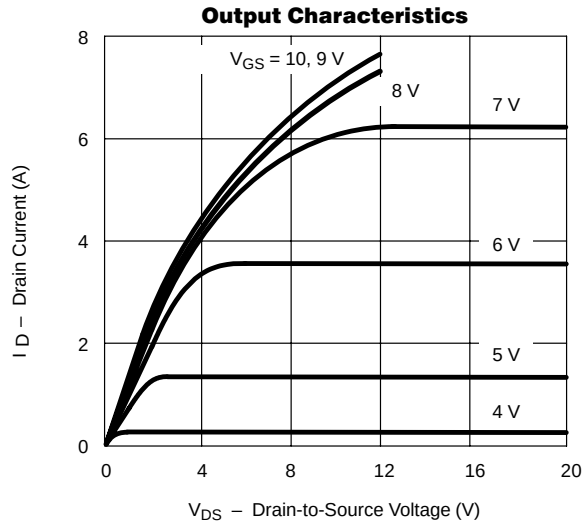
## Notes

A. Guaranteed by design, not subject to production testing.

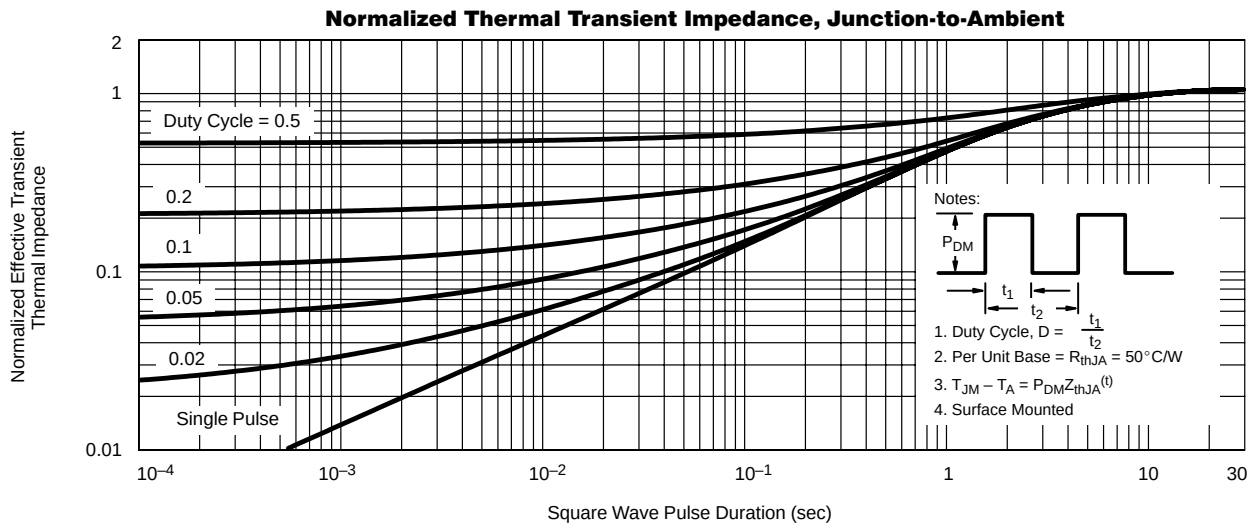
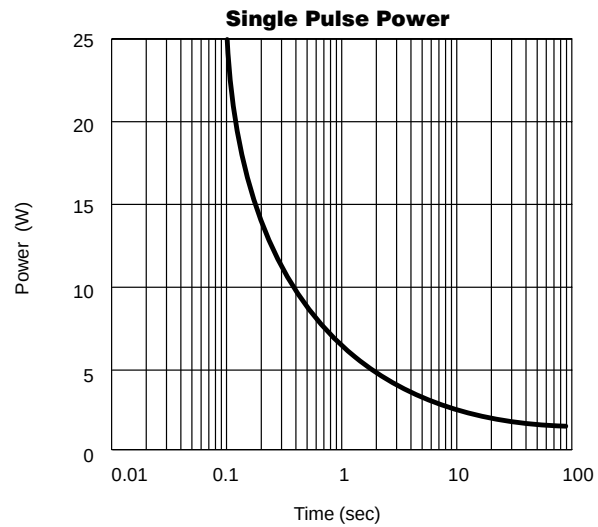
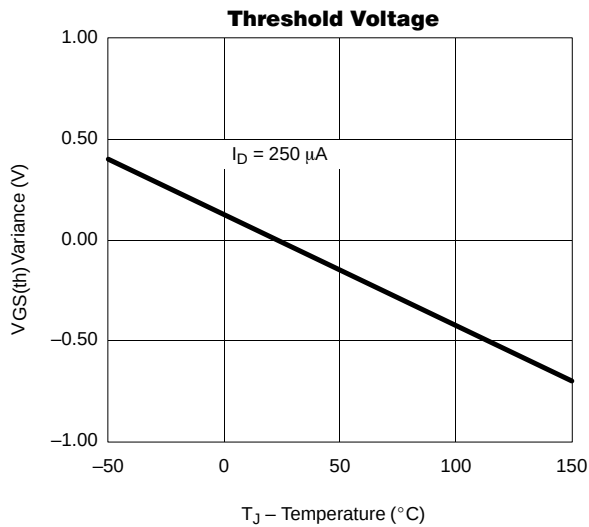
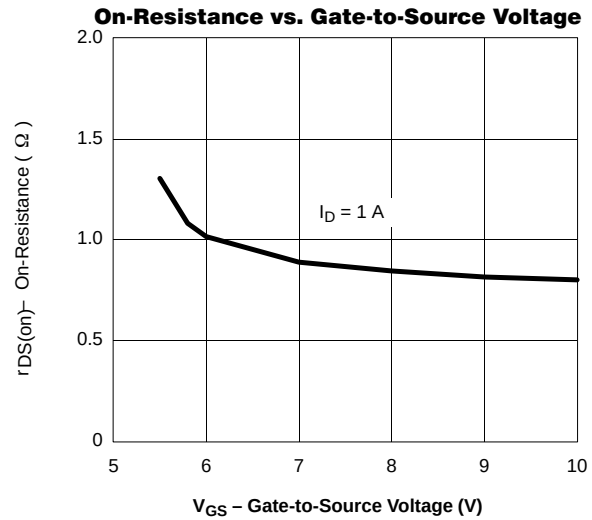
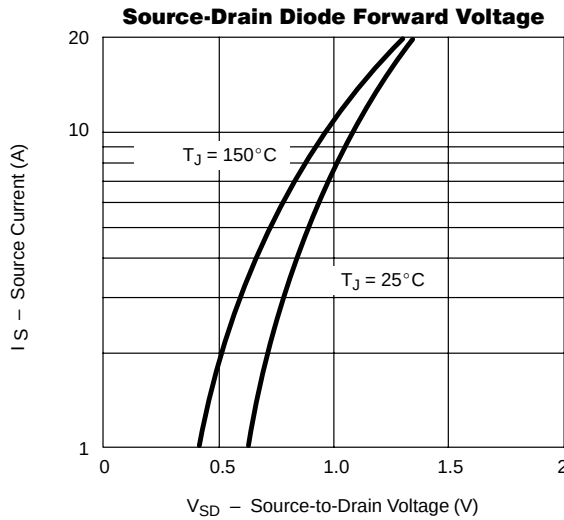
B. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.



### TYPICAL CHARACTERISTICS (25°C UNLESS OTHERWISE NOTED)



## TYPICAL CHARACTERISTICS (25°C UNLESS OTHERWISE NOTED)





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